

Amendments to the Specification:

Please replace the paragraph beginning at page 6, line 7, with the following amended paragraph:

Accordingly, a bit line can be arranged above the ridge, can run parallel to the longitudinal direction of the ridge, and can be connected to the second source/drain region. By this bit line, ridges, which are arranged along their longitudinal direction adjacent to one another and separated by capacitor trenches, can be connected ~~to the bit line~~. The contact is made through a bit line contact disposed at a respective end of the ridge. In the direction of the word lines adjacent to the ridges and at a level below the bit lines, provided that no word lines run there, the memory cell array can be filled with an insulating material, for example, an oxide or nitride.